

# IRFBA90N20DPbF

HEXFET® Power MOSFET

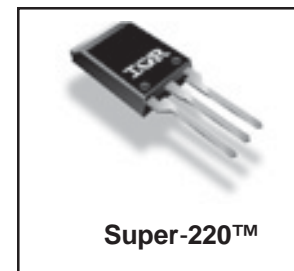
## Applications

- High frequency DC-DC converters
- Lead-Free

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on) max</sub></b>	<b>I<sub>D</sub></b>
<b>200V</b>	<b>0.023Ω</b>	<b>98A<sup>Ⓒ</sup></b>

## Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



## Absolute Maximum Ratings

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	98 <sup>Ⓒ</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	71 <sup>Ⓒ</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>Ⓓ</sup>	390	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	650	W
	Linear Derating Factor	4.3	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt <sup>Ⓔ</sup>	6.3	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Recommended Clip Force	20	N

## Thermal Resistance

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	0.23	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient	—	58	

Notes <sup>Ⓓ</sup> through <sup>Ⓔ</sup> are on page 8

## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	200	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.22	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.023	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 59A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -30V

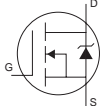
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

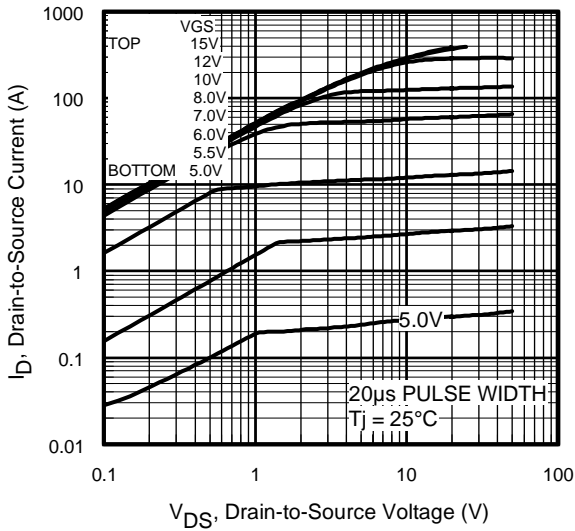
	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	41	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 59A
Q <sub>g</sub>	Total Gate Charge	—	160	240	nC	I <sub>D</sub> = 59A
Q <sub>gs</sub>	Gate-to-Source Charge	—	45	67		V <sub>DS</sub> = 160V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	75	110		V <sub>GS</sub> = 10V ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	23	—	ns	V <sub>DD</sub> = 100V
t <sub>r</sub>	Rise Time	—	160	—		I <sub>D</sub> = 59A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	39	—		R <sub>G</sub> = 1.2Ω
t <sub>f</sub>	Fall Time	—	77	—		V <sub>GS</sub> = 10V ④
C <sub>iss</sub>	Input Capacitance	—	6080	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	1040	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	150	—		f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	7500	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	410	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 160V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	790	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 160V ⑤

## Avalanche Characteristics

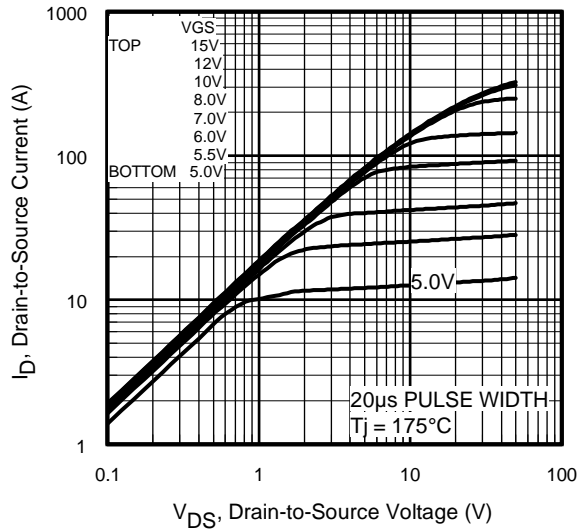
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	960	mJ
I <sub>AR</sub>	Avalanche Current①	—	59	A
E <sub>AR</sub>	Repetitive Avalanche Energy①	—	65	mJ

## Diode Characteristics

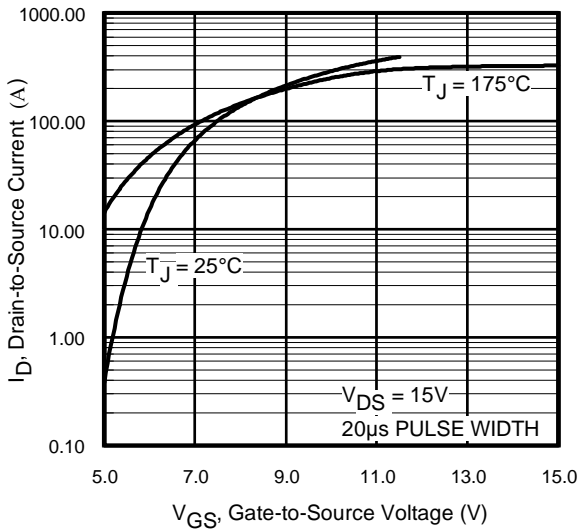
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	98	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	390		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.5	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 59A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	220	340	nS	T <sub>J</sub> = 25°C, I <sub>F</sub> = 59A
Q <sub>rr</sub>	Reverse Recovery Charge	—	1.9	2.8	μC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				



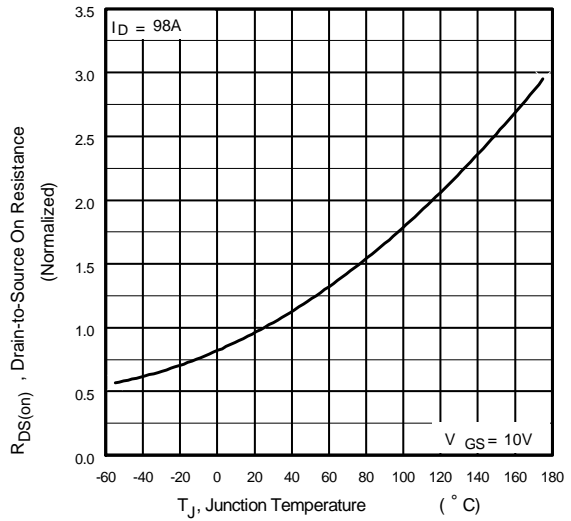
**Fig 1.** Typical Output Characteristics



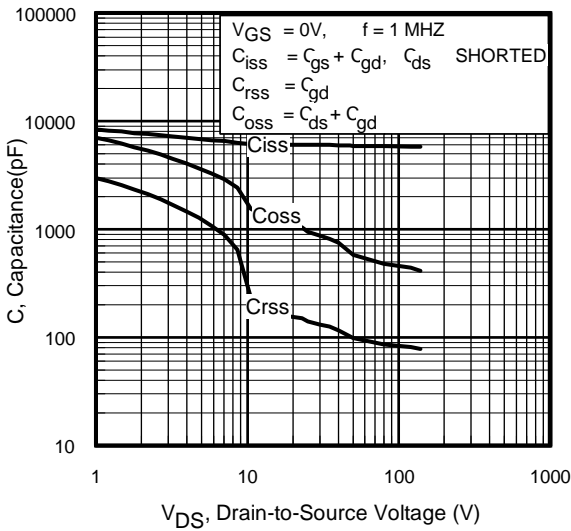
**Fig 2.** Typical Output Characteristics



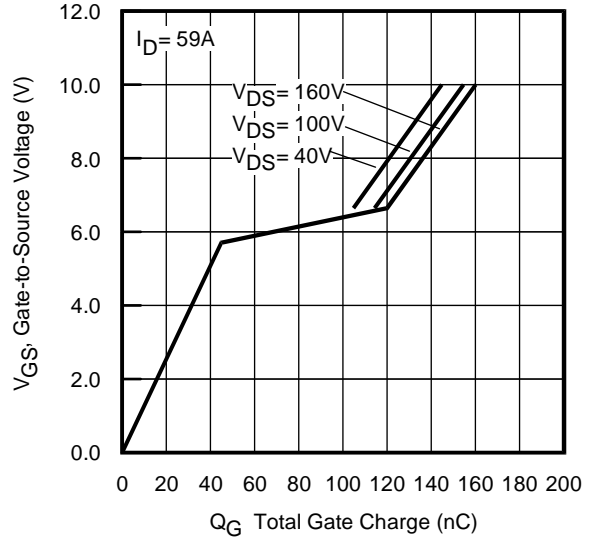
**Fig 3.** Typical Transfer Characteristics



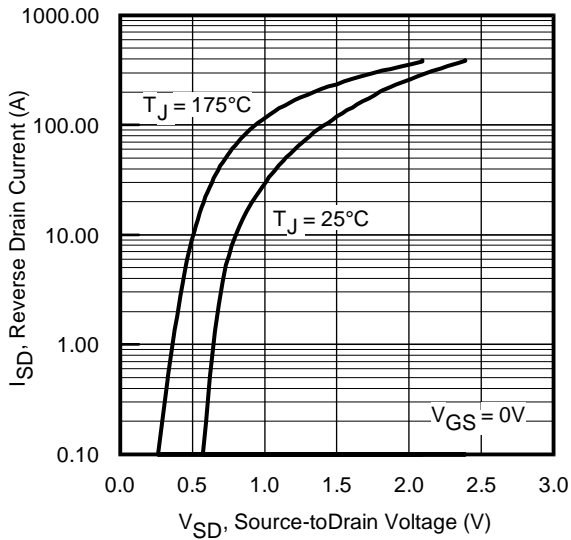
**Fig 4.** Normalized On-Resistance Vs. Temperature



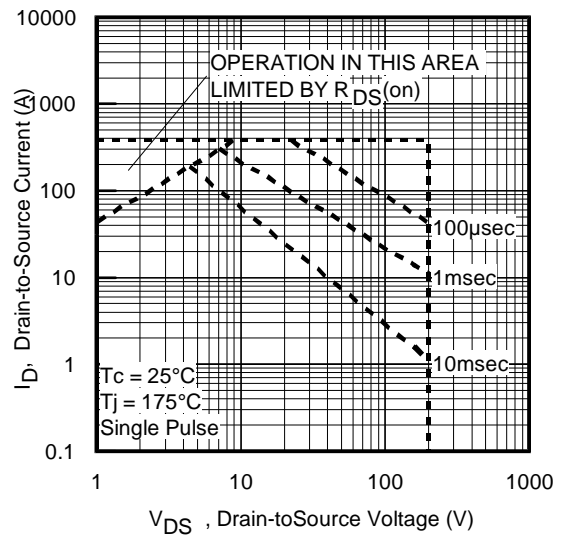
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

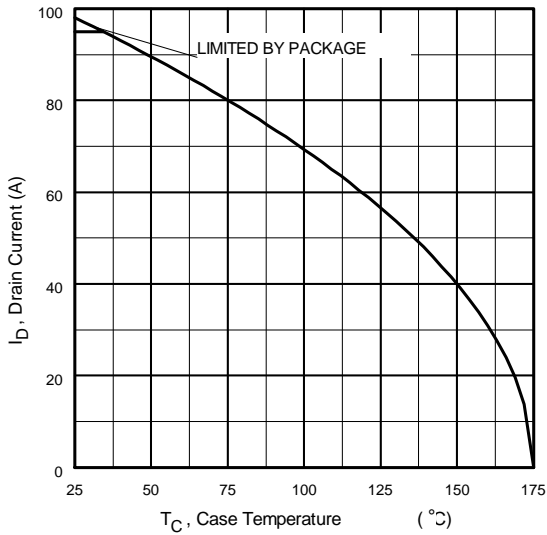


Fig 9. Maximum Drain Current Vs. Case Temperature



Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

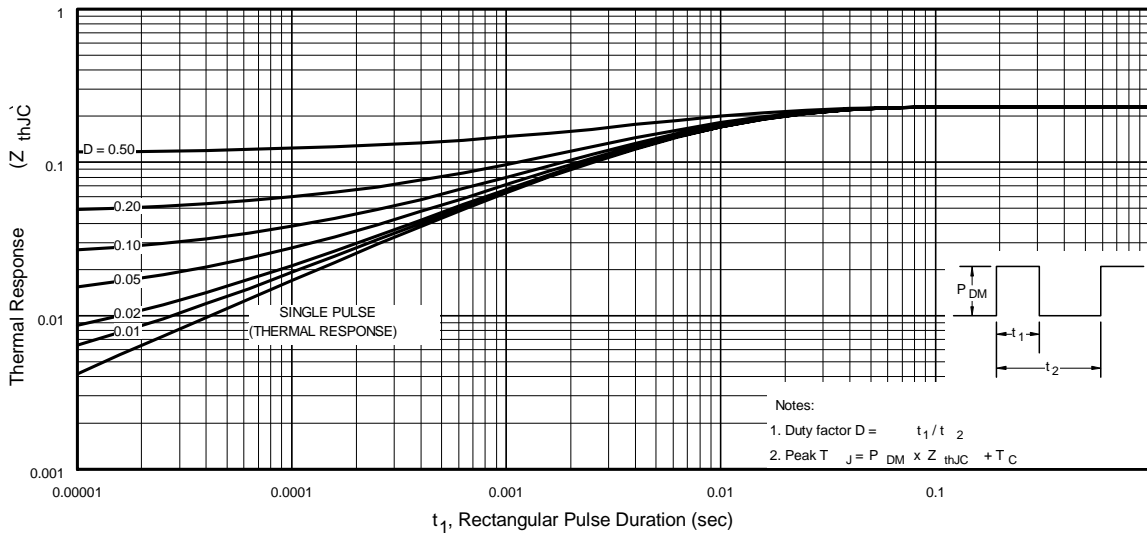
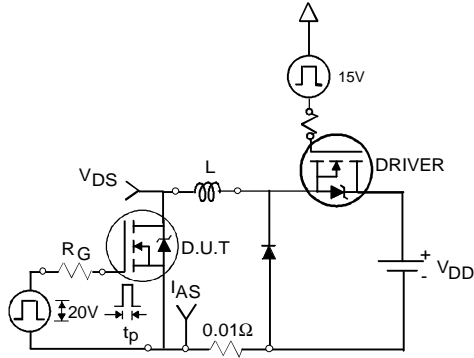
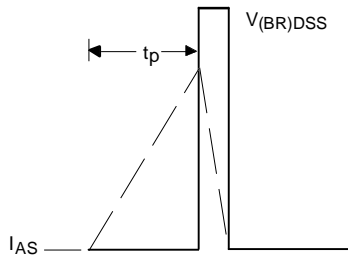


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

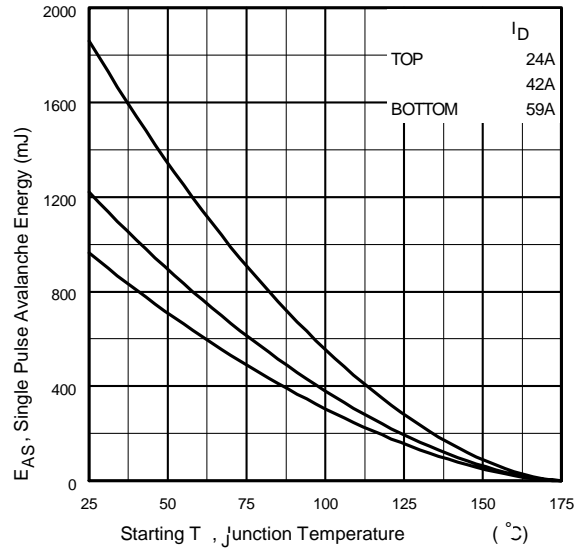
# IRFBA90N20DPbF



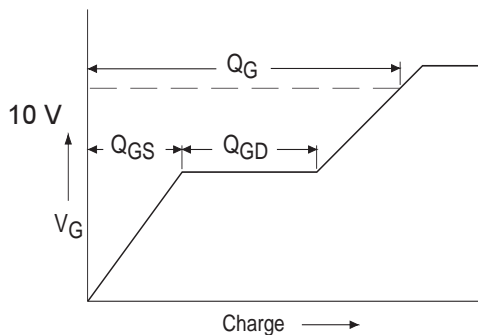
**Fig 12a.** Unclamped Inductive Test Circuit



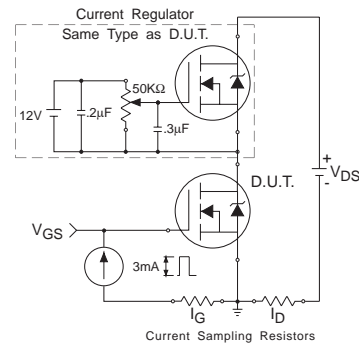
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

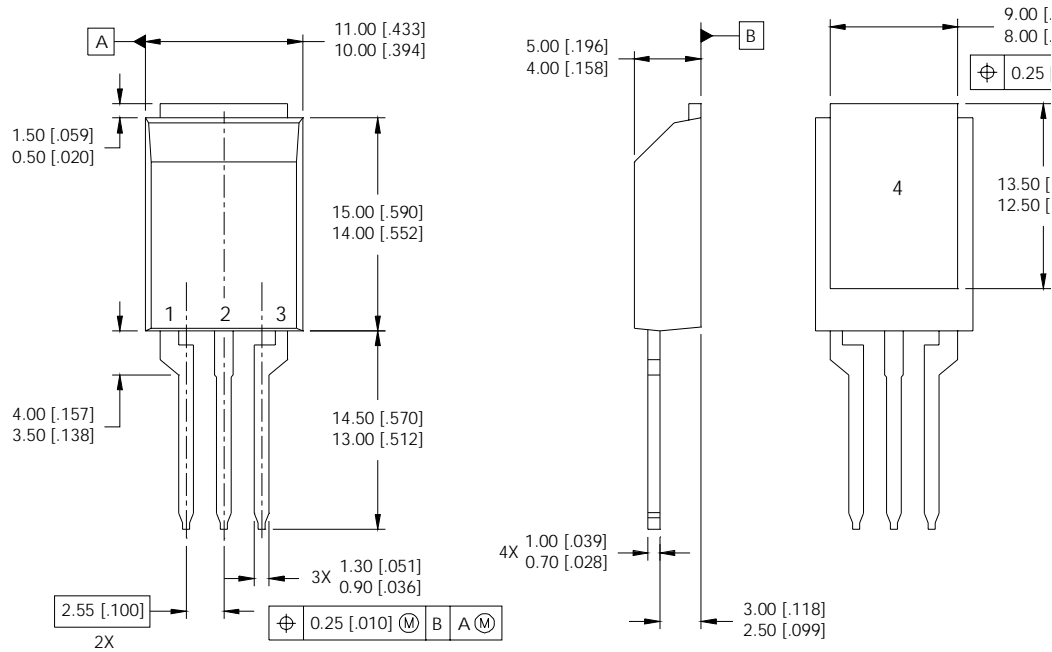
**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFET® Power MOSFETs

## Super-220™ ( TO-273AA ) Package Outline



**NOTES:**

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-273AA.

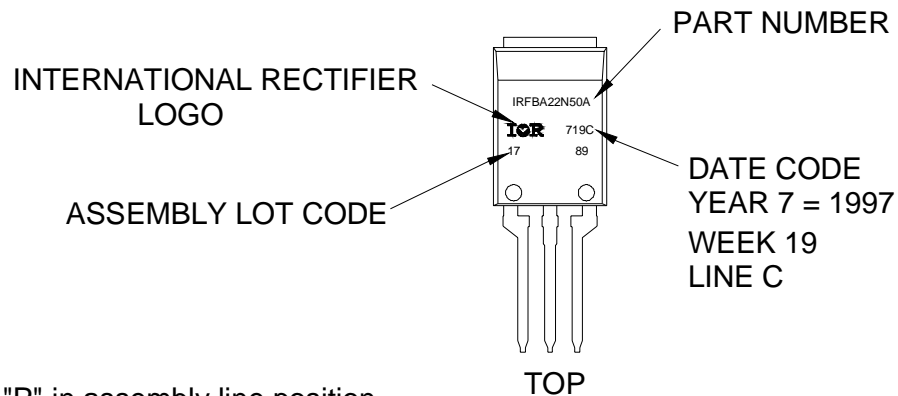
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.55\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 59\text{A}$ .
- ③  $I_{SD} \leq 59\text{A}$ ,  $di/dt \leq 170\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 95A.



## Super-220 (TO-273AA) Part Marking Information

EXAMPLE: THIS IS AN IRFBA22N50A WITH  
ASSEMBLY LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position  
indicates "Lead-Free"

**Super-220™ not recommended for surface mount application.**

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

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